Elektronische Bauelemente

SSD86N06SV-C

86A, 60V, $R_{DS(ON)}$ 3.6mΩ

N-Channel Shielded Gate Trench Power MOSFET

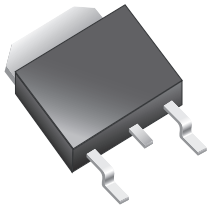
RoHS Compliant Product
A suffix of "-C" specifies halogen free

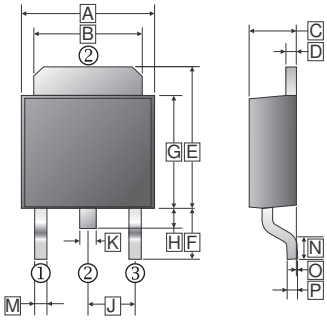
DESCRIPTION

The SSD86N06SV-C is the Shielded Gate Technology N-Ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SSD86N06SV-C meet the RoHS and Green Product requirement with full function reliability approved.

TO-252(D-Pack)





FEATURES

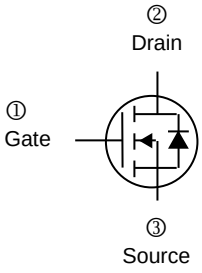
- Shielded Gate Trench Technology
- Super Low Gate Charge
- Green Device Available

MARKING

86N06SV
□□□□
□ = Date Code

PACKAGE INFORMATION

Package	MPQ	Leader Size
TO-252	2.5K	13 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.3	6.9	J	2.3 REF.	
B	4.95	5.53	K	0.89 REF.	
C	2.1	2.5	M	0.45	1.14
D	0.4	0.9	N	1.55 Typ.	
E	6	7.7	O	0	0.15
F	2.90 REF		P	0.58 REF.	
G	5.4	6.4			
H	0.6	1.2			

ORDER INFORMATION

Part Number	Type
SSD86N06SV-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1] @V_{GS}=10V	T_C=25℃	I_D	86	A
	T_C=100℃		55	
Pulsed Drain Current [2 3]		I_{DM}	190	A
Total Power Dissipation [1]	T_C=25℃	P_D	52	W
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55~150	℃
Thermal Resistance Ratings				
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	62	℃/W
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	2.4	

ELECTRICAL CHARACTERISTICS (T_J=25℃ unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		BV_{DSS}	60	-	-	V	V_{GS}=0, I_D=250μA
Gate Threshold Voltage		$V_{GS(th)}$	2	-	4	V	V_{DS}=V_{GS}, I_D=250μA
Forward Transconductance		g_{fs}	-	65	-	S	V_{DS}=5V, I_D=15A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current	T_J=25℃	I_{DSS}	-	-	1	μA	V_{DS}=48V, V_{GS}=0
	T_J=55℃		-	-	5		V_{DS}=48V, V_{GS}=0
Static Drain-Source On-Resistance [3]		$R_{DS(ON)}$	-	3	3.6	mΩ	V_{GS}=10V, I_D=15A
			-	3.9	5.2		V_{GS}=7V, I_D=10A
Total Gate Charge		Q_g	-	59	-	nC	I_D=15A V_{DS}=30V V_{GS}=10V
Gate-Source Charge		Q_{gs}	-	15	-		
Gate-Drain Change		Q_{gd}	-	10	-		
Turn-on Delay Time		$T_{d(on)}$	-	20	-	nS	V_{DD}=30V I_D=15A V_{GS}=10V R_G=3Ω
Rise Time		T_r	-	9	-		
Turn-off Delay Time		$T_{d(off)}$	-	60	-		
Fall Time		T_f	-	15	-		
Input Capacitance		C_{iss}	-	3509	-	pF	V_{GS}=0 V_{DS}=30V f=1MHz
Output Capacitance		C_{oss}	-	1175	-		
Reverse Transfer Capacitance		C_{rss}	-	68	-		
Source-Drain Diode							
Diode Forward Voltage [3]		V_{SD}	-	-	1.2	V	V_{GS}=0, I_S=1A
Continuous Source Current [1]		I_S	-	-	86	A	
Pulsed Source Current [2 3]		I_{SM}	-	-	190	A	
Reverse Recovery Time		T_{rr}	-	24	-	nS	I_F=15A, dI/dt=100A/μs, T_J=25℃
Reverse Recovery Charge		Q_{rr}	-	85	-	nC	

Notes:
1. The data tested by surface mounted on 1inch^2 FR4 Board with 2OZ copper.
2. The power dissipation is limited by 150℃, junct ion temperature.
3. The data tested by pulsed, Pulse Width≦300μs, Duty Cycle≦2%.

TYPICAL CHARACTERISTICS CURVE

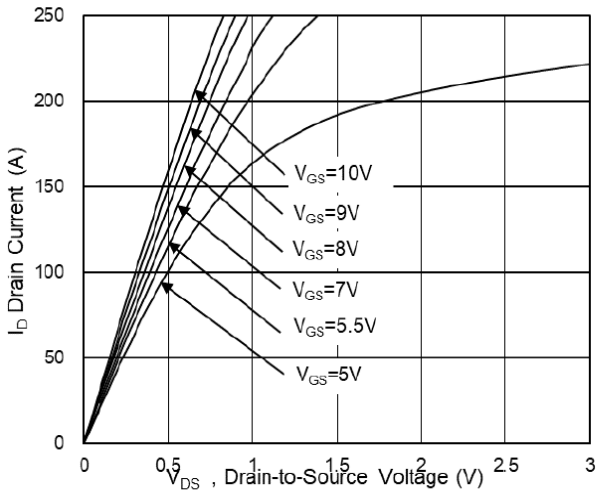


Fig.1 Typical Output Characteristics

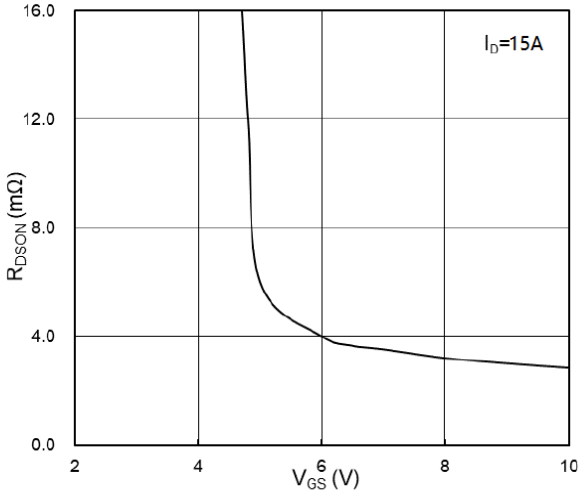


Fig.2 On-Resistance vs G-S Voltage

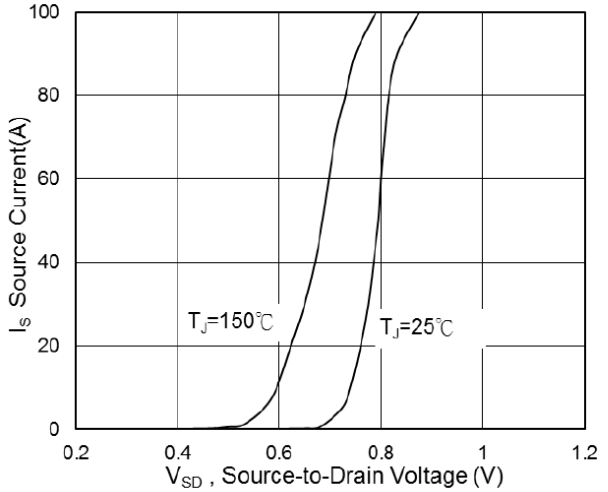


Fig.3 Diode Forward Voltage vs Current

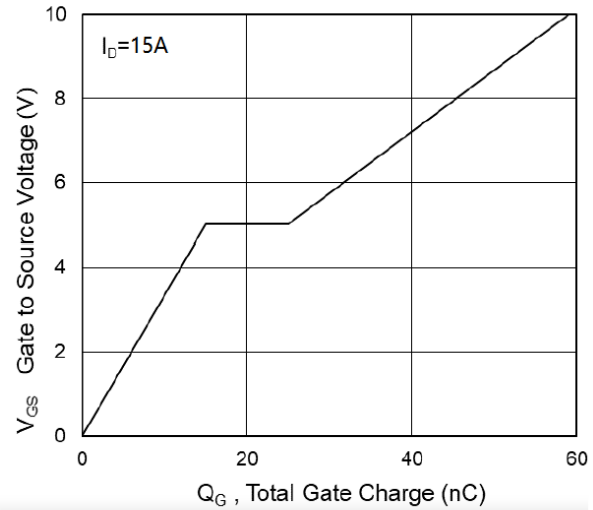


Fig.4 Gate-Charge Characteristics

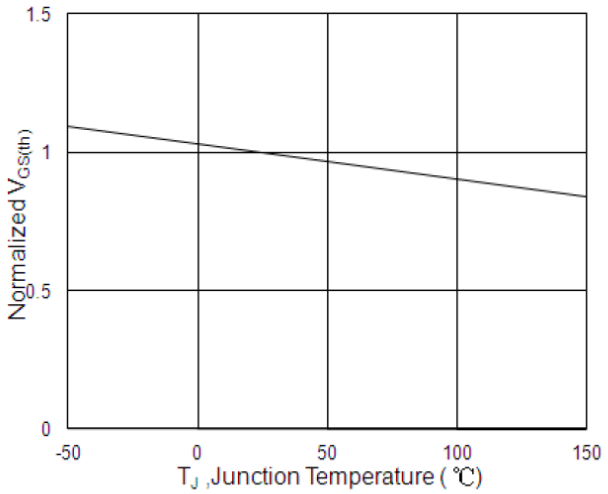


Fig.5 Normalized $V_{GS(th)}$ vs T_J

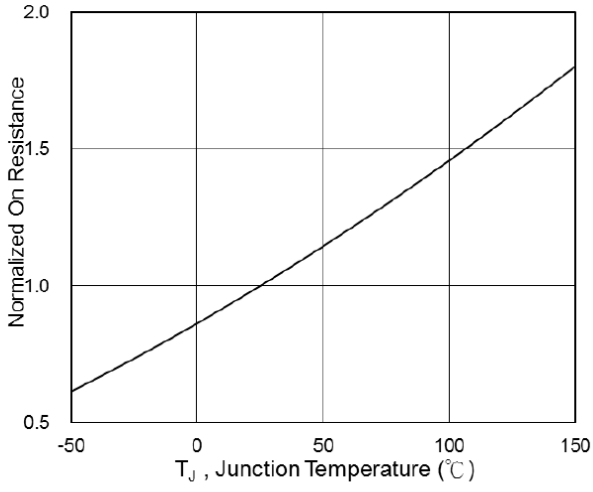


Fig.6 Normalized R_{DSON} vs T_J

TYPICAL CHARACTERISTICS CURVE

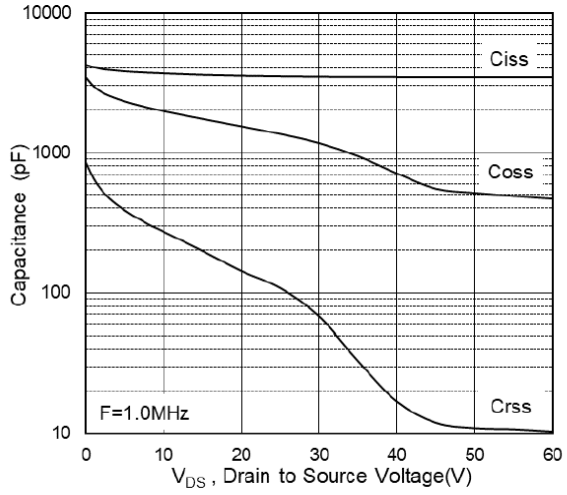


Fig.7 Capacitance

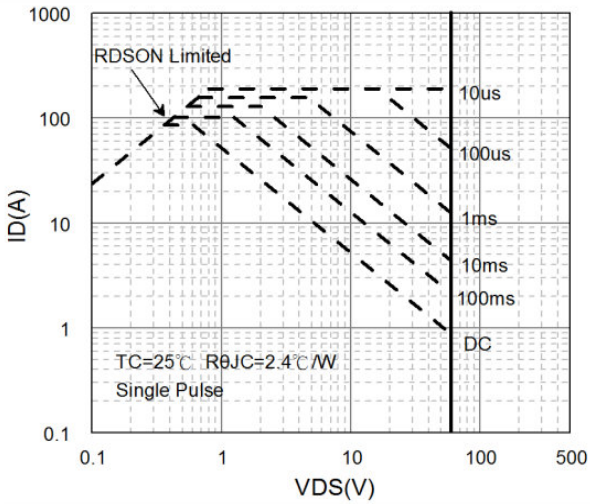


Fig.8 Safe Operating Area

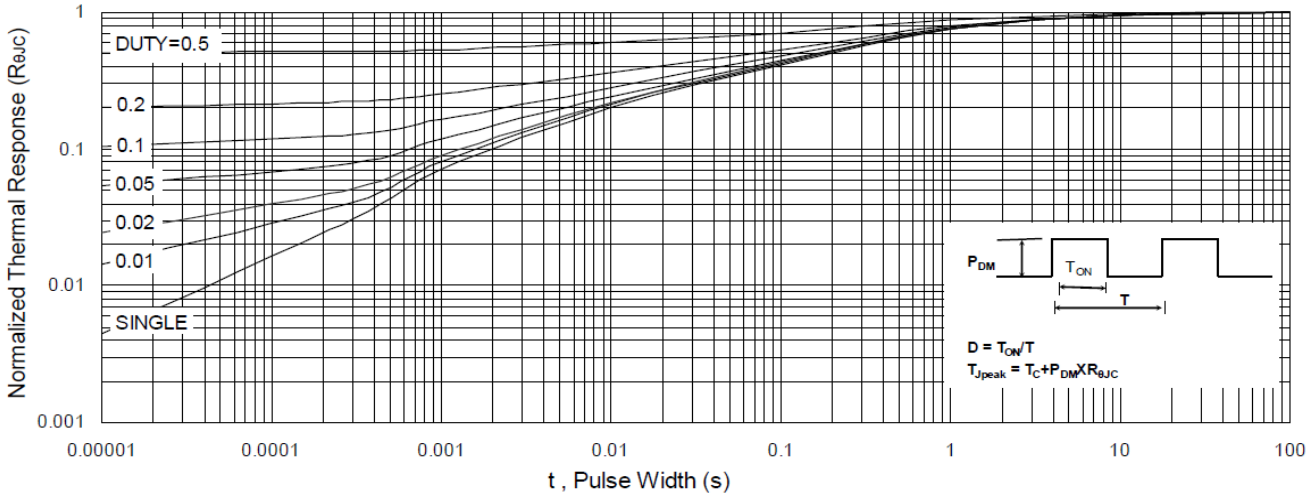


Fig.9 Normalized Maximum Transient Thermal Impedance

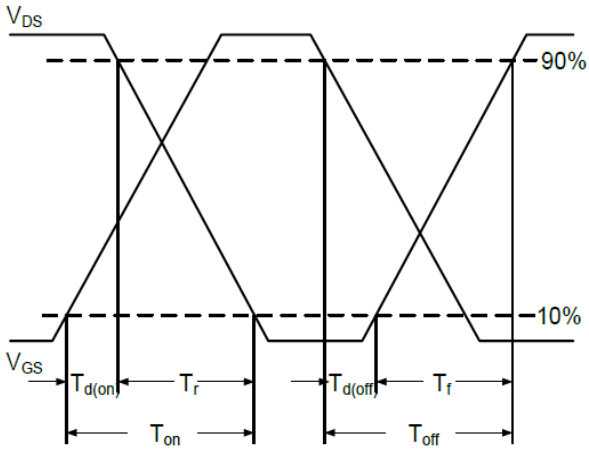


Fig.10 Switching Time Waveform

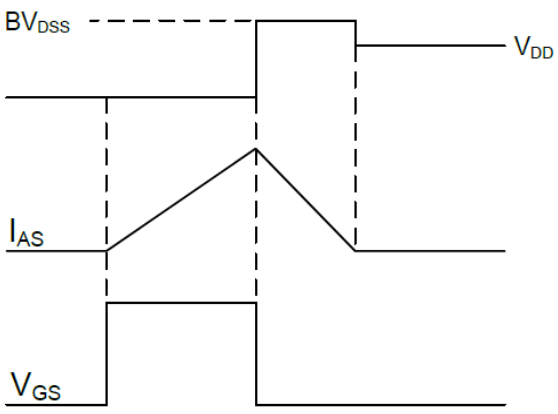


Fig.11 Unclamped Inductive Waveform